

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	4197	(257/66,65,19,77,18,250,202).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/04/06 13:13
L2	282	finfet	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/04/06 16:07
L3	4185	1 not 2	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/04/06 13:14
L4	3865	3 and (@ad<"20040331")	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/04/06 13:14
L5	10	4 and (SiGe) and (SiC or (silicon adj carbide)) and (cap or capping) and (tensile and compressive)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/04/06 13:22
L6	7	4 and (SiGe) and (SiC or (silicon adj carbide)) and (tensile and compressive) not 5	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/04/06 13:20

L7	103	4 and (SiGe) and (SiC or (silicon adj carbide)) not 5	US-PPGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/04/06 13:58
L8	13	(finfet) and (SiGe) and (SiC or (silicon adj carbide)) not 5	US-PPGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/04/06 14:09
L9	25	(SiC same SiGe) and (transistor\$1) and (body) and (cap or capping) and (gate adj electrode)	US-PPGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/04/06 14:44
L10	16	(transistor) and (body same (SiC and SiGe))	US-PPGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/04/06 15:11
L11	902	(transistor) and ((SiC and SiGe))	US-PPGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/04/06 15:11
L12	837	(transistor) and ((SiC and SiGe)) not 7	US-PPGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/04/06 15:13

L13	783	12 and (@ad<"20040331")	US-PPGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/04/06 15:13
L14	590	(transistor) and ((SiC same SiGe)) not 7	US-PPGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/04/06 15:13
L15	552	14 and (@ad<"20040331")	US-PPGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/04/06 15:30
L16	52	15 and (Si same (cap or capping))	US-PPGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/04/06 15:30
L17	66	2 and (cap or capping)	US-PPGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/04/06 16:07
L18	327	(257/e29.193).CCLS.	US-PPGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/04/06 16:33

L19	0	("18and(@ad<20040331")).PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/04/06 16:33
L20	0	("18and(@ad<20040331")).PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/04/06 16:33
L21	315	18 and (@ad<"20040331")	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/04/06 16:57
L22	80	(finfet) and ((SiGe) same (Si or silicon))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/04/06 16:57
L23	76	(finfet) and ((SiGe) same (Si or silicon)) and (@ad<"20040331")	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/04/06 16:58
L24	66	(finfet) and ((SiGe) same (silicon)) and (@ad<"20040331")	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/04/06 16:59

L25	76	((finfet) and ((SiGe) same (Si or silicon)) and (@ad < "20040331")	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/04/06 16:59
S1	27	((SiGe or SiC) same (body)) and ((cap or capping) same (Si or silicon)) and (gate adj electrode) and (substrate) and (@ad < "20040331")	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/04/06 10:42
S2	282	finfet	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/04/06 13:13
S3	20	S2 and (SiC or (silicon adj carbide))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/04/06 13:12
S4	4197	(257/66,65,19,77,18,250,202).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/04/06 13:13